BUK963R2-40B

N-channel TrenchMOS logic level FET

13 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	300	W
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C		-	2.4	2.8	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11; Fig. 12		-	2.7	3.2	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 32 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 13$		-	37	-	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruugedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 100 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	1.2	J

[1] All individual parts of device must be ≤ 175 °C to achieve maximum current rating.

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G C C
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

[1] It is not possible to make connection to pin 2.

Ordering information

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
BUK963R2-40B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

Marking

Table 4. **Marking codes**

Type number	Marking code
BUK963R2-40B	BUK963R2-40B

Limiting values 8.

Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	40	V

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Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage			-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	300	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	222	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[2]	-	100	Α
		T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	[2]	-	100	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	888	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-dra	in diode	'				
Is	source current	T _{mb} = 25 °C	[1]	-	222	Α
			[2]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	888	Α
Avalanche	ruugedness	•		,		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le$ 40 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	1.2	J

- [1] Current is limited by power dissipation chip rating.
- [2] All individual parts of device must be ≤ 175 °C to achieve maximum current rating.

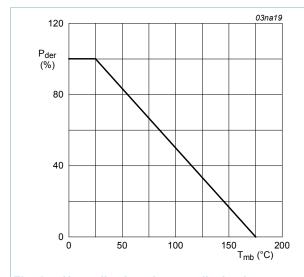


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

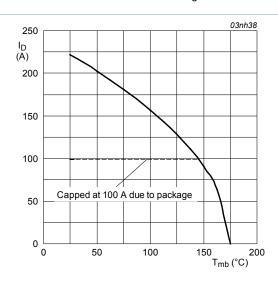


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

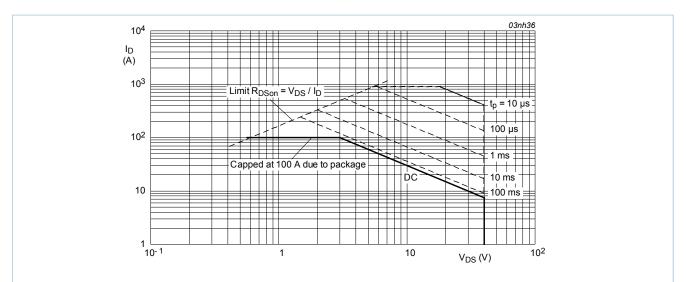


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25$$
°C; I_{DM} is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

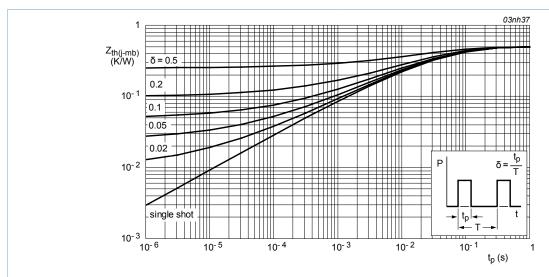


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		'	<u> </u>		,
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	36	-	-	٧
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	40	-	-	٧
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10	1.1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μΑ
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
200	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	2.4	2.8	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	3.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	6	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12	-	2.7	3.2	mΩ
Dynamic o	characteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 5 V;	-	94	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u>	-	17	-	nC
Q_{GD}	gate-drain charge		-	37	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	7877	10502	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	1397	1676	pF
C _{rss}	reverse transfer capacitance		-	608	833	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 5 V;	-	68	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	268	-	ns
t _{d(off)}	turn-off delay time		-	257	-	ns
t _f	fall time		-	192	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to center of die; T _i = 25 °C	-	4.5	-	nΗ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		from upper edge of drain mounting base to center of die; T _j = 25 °C	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nH
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 40 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; Fig. 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	70	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	127	-	nC

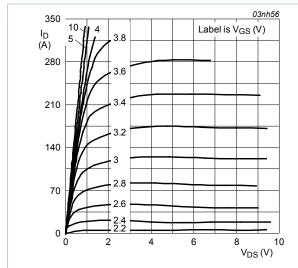


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



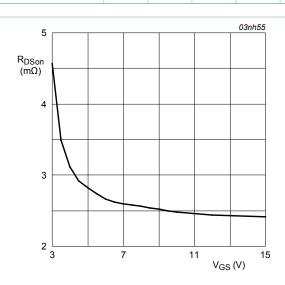


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

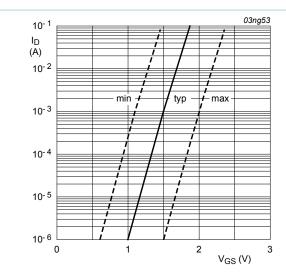


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,{}^{\circ}C; V_{DS} = V_{GS}$$

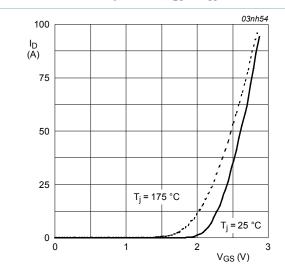


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS}=25V$$

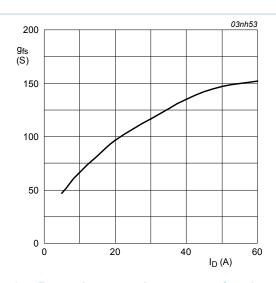


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

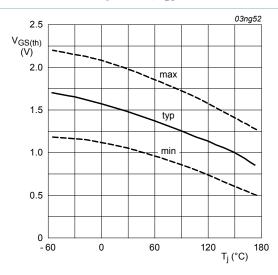


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

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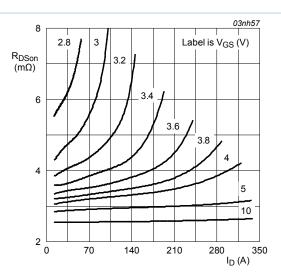


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

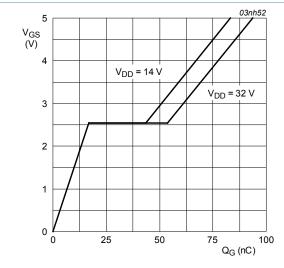


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; V_{DS} = 25V$$

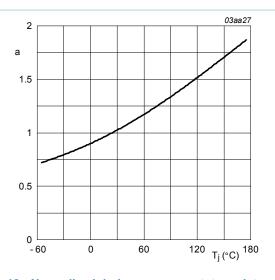


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

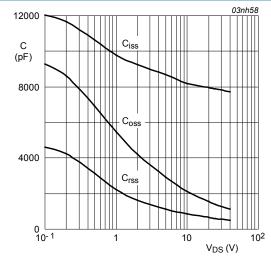


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

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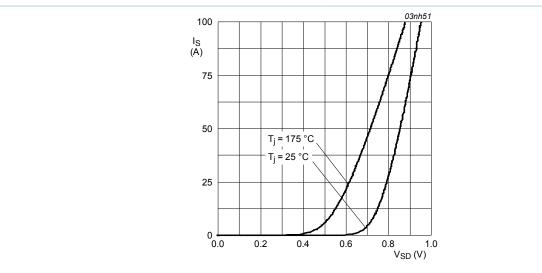
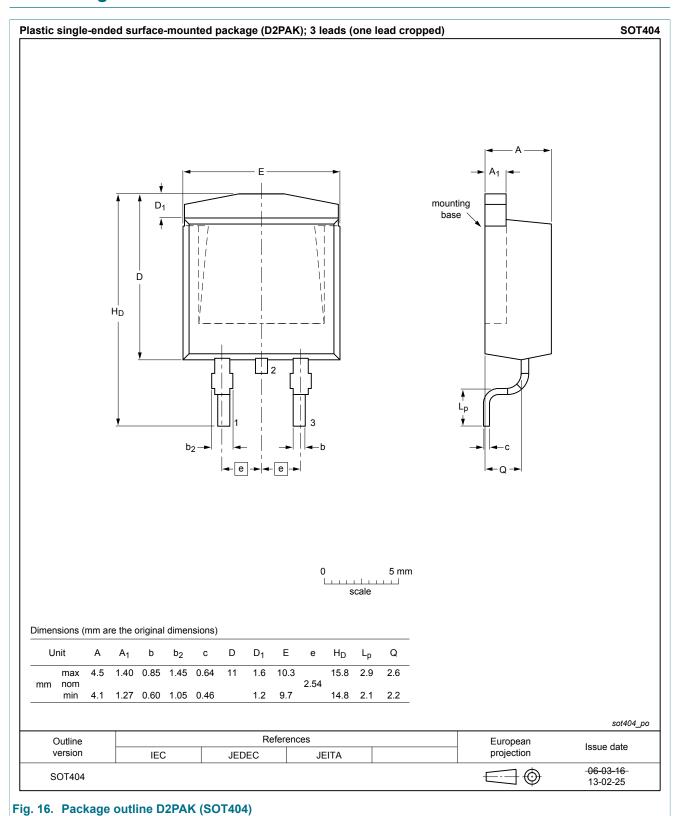


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{\it GS} = 0V$$

11. Package outline



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